FIG. 1

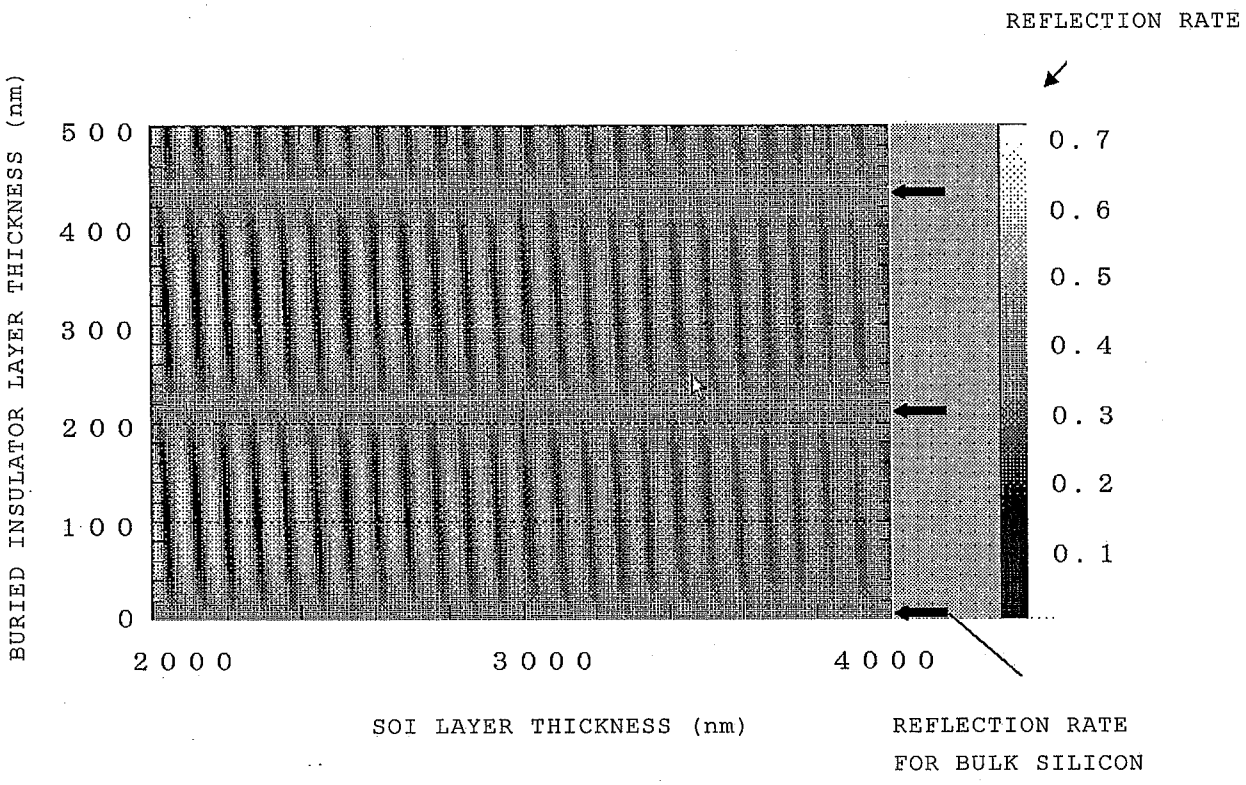

REFLECTION RATE
BURIED INSULATOR LAYER THICKNESS (nm)
500
400
300
200
100
0
2000
3000
4000
0.7
0.6
0.5
0.4
0.3
0.2
0.1
SOI LAYER THICKNESS (nm)
REFLECTION RATE
FOR BULK SILICON

FIG. 2

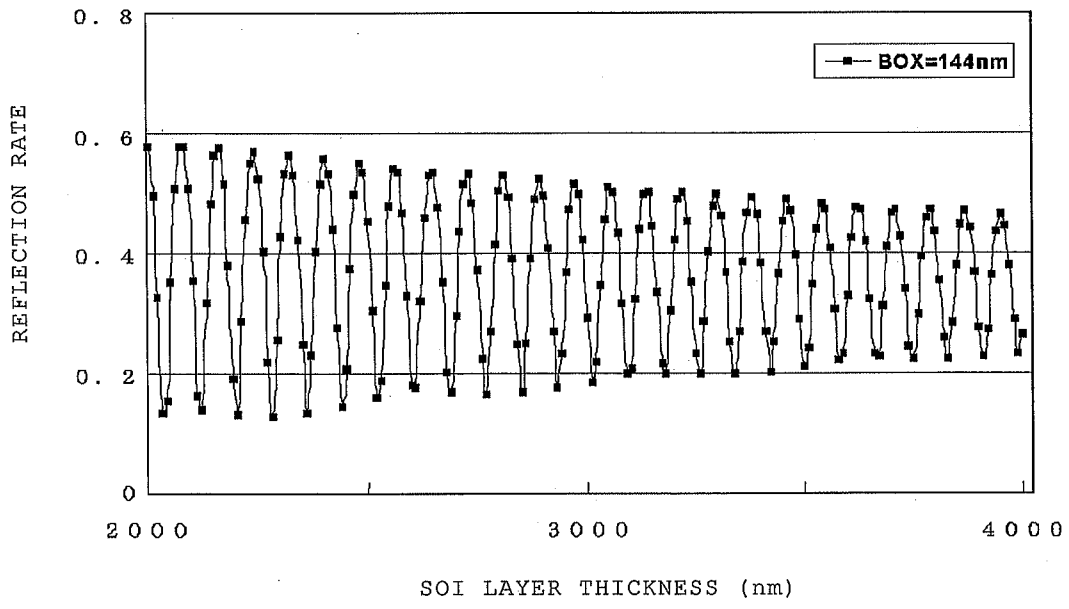

REFLECTION RATE
0.8
0.6
0.4
0.2
0
BOX=144nm
2000
3000
4000
SOI LAYER THICKNESS (nm)

FIG. 3

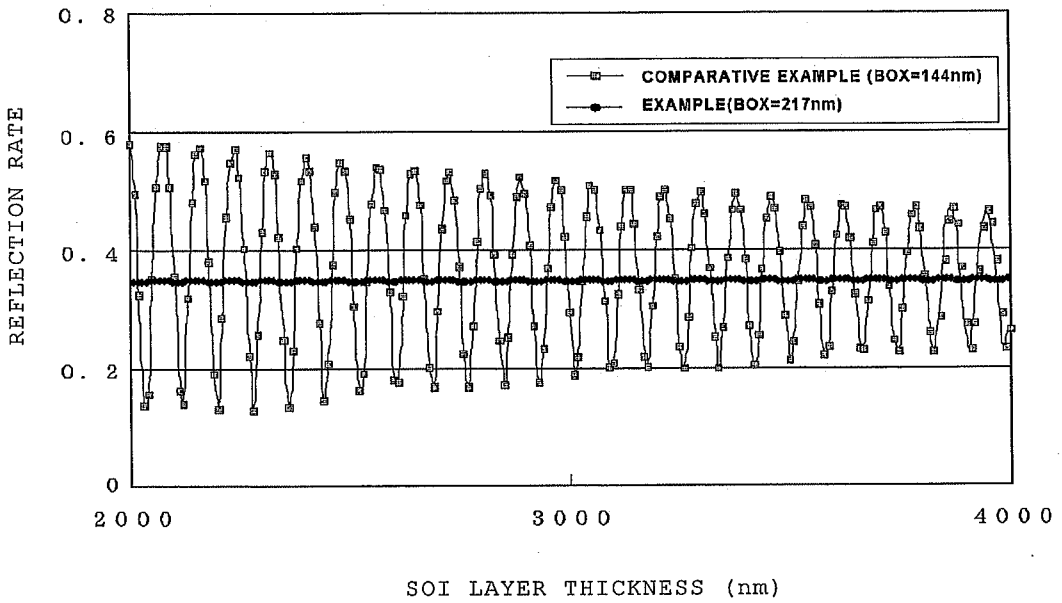

0.8
0.6
0.4
0.2
0
REFLECTION RATE
COMPARATIVE EXAMPLE (BOX=144nm)
EXAMPLE(BOX=217nm)
2000
3000
4000
SOI LAYER THICKNESS (nm)

FIG. 4

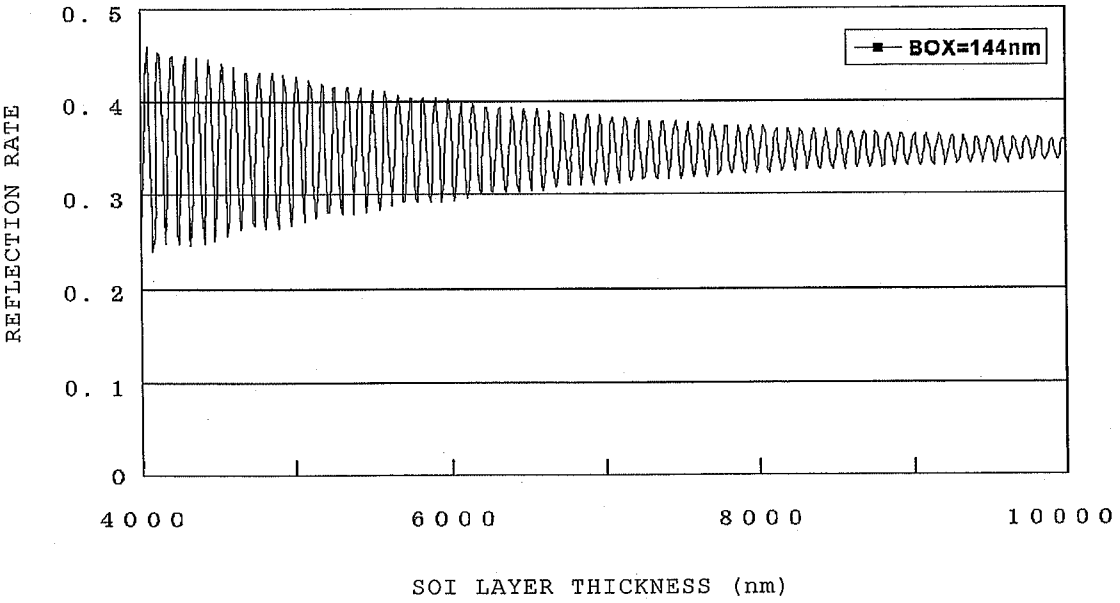

0.5
0.4
0.3
0.2
0.1
0
REFLECTION RATE
BOX=144nm
4000
6000
8000
10000
SOI LAYER THICKNESS (nm)

FIG. 5

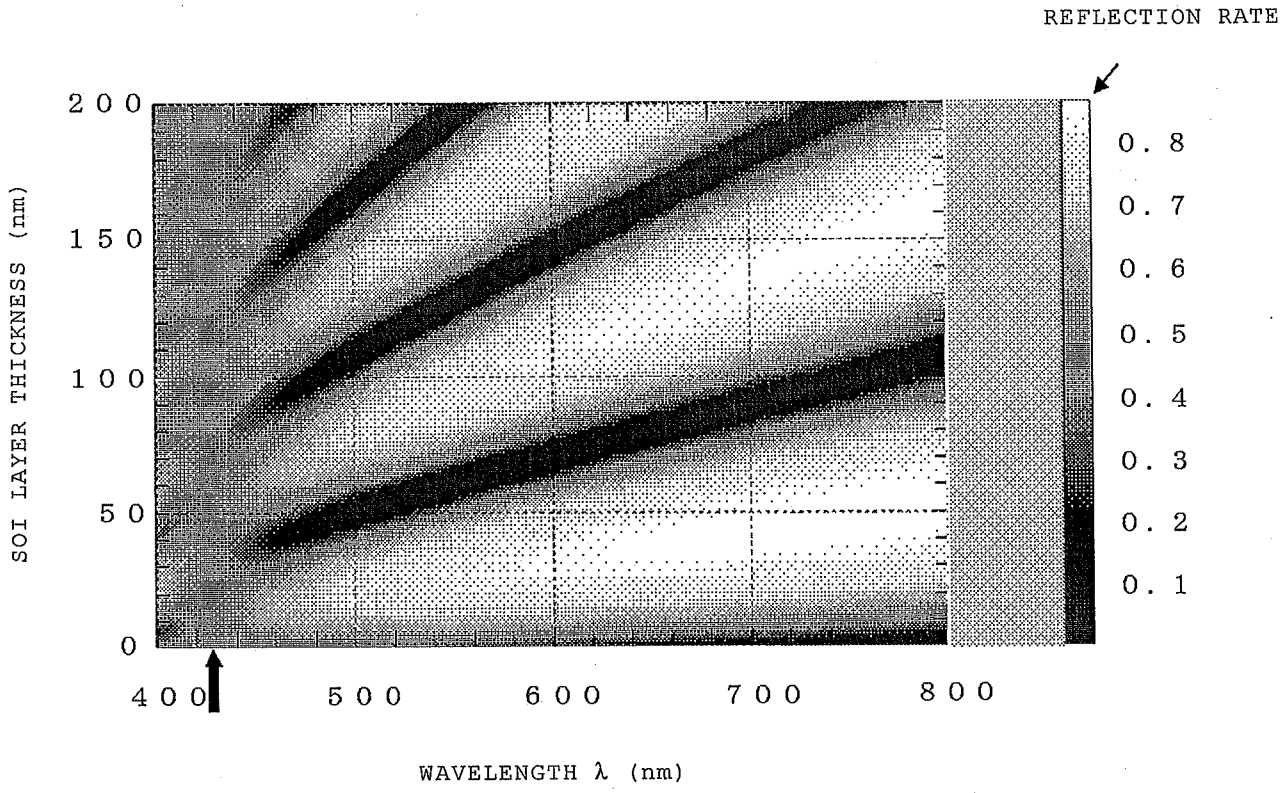
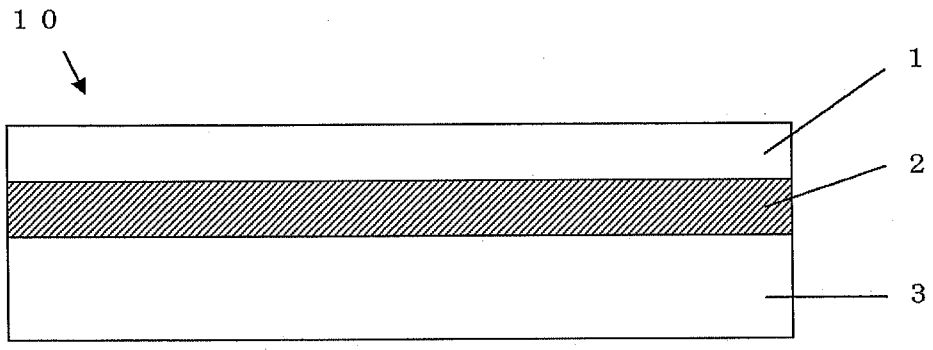

REFLECTION RATE
0.8
0.7
0.6
0.5
0.4
0.3
0.2
0.1
SOI LAYER THICKNESS (nm)
200
150
100
50
0
400
500
600
700
800
WAVELENGTH λ (nm)

FIG. 6


10
1
2
3